Zhang Baoping

List of Publications by Year in descending order

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516561 434063 1,072 60 16 31 citations g-index h-index papers 61 61 61 1003 docs citations times ranked citing authors all docs

| # | Article | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Effects of single and combined UV-LEDs on inactivation and subsequent reactivation of E.Âcoli in water disinfection. Water Research, 2018, 147, 331-341. | 5.3 | 131 |
| 2 | Quantum dot vertical-cavity surface-emitting lasers covering the â€~green gap'. Light: Science and Applications, 2017, 6, e16199-e16199. | 7.7 | 92 |
| 3 | Room temperature continuous wave lasing of electrically injected GaN-based vertical cavity surface emitting lasers. Applied Physics Letters, 2014, 104, . | 1.5 | 78 |
| 4 | Highâ€Efficiency Allâ€Dielectric Metalenses for Midâ€Infrared Imaging. Advanced Optical Materials, 2017, 5, 1700585. | 3.6 | 75 |
| 5 | Comparison of the performance of pulsed and continuous UVC-LED irradiation in the inactivation of bacteria. Water Research, 2019, 157, 218-227. | 5.3 | 64 |
| 6 | Low threshold continuous-wave lasing of yellow-green InGaN-QD vertical-cavity surface-emitting lasers. Optics Express, 2016, 24, 15546. | 1.7 | 57 |
| 7 | Progress and prospects of GaN-based VCSEL from near UV to green emission. Progress in Quantum Electronics, 2018, 57, 1-19. | 3.5 | 54 |
| 8 | Efficient hole transport in asymmetric coupled InGaN multiple quantum wells. Applied Physics Letters, 2009, 95, . | 1.5 | 51 |
| 9 | Strong localization effect and carrier relaxation dynamics in self-assembled InGaN quantum dots emitting in the green. Nanoscale Research Letters, 2015, 10, 31. | 3.1 | 51 |
| 10 | Efficacy of UVC-LED in water disinfection on Bacillus species with consideration of antibiotic resistance issue. Journal of Hazardous Materials, 2020, 386, 121968. | 6.5 | 40 |
| 11 | Advances in application of ultraviolet irradiation for biofilm control in water and wastewater infrastructure. Journal of Hazardous Materials, 2022, 421, 126682. | 6.5 | 40 |
| 12 | Spectral dynamics of picosecond gain-switched pulses from nitride-based vertical-cavity surface-emitting lasers. Scientific Reports, 2014, 4, 4325. | 1.6 | 25 |
| 13 | Inorganic Lead-Free B-Î ³ -CsSnI ₃ Perovskite Solar Cells Using Diverse Electron-Transporting Materials: A Simulation Study. ACS Omega, 2021, 6, 26689-26698. | 1.6 | 24 |
| 14 | A comparative study of thermal characteristics of GaN-based VCSELs with three different typical structures. Semiconductor Science and Technology, 2018, 33, 015016. | 1.0 | 24 |
| 15 | Low Threshold Lasing of GaN-Based VCSELs With Sub-Nanometer Roughness Polishing. IEEE Photonics Technology Letters, 2013, 25, 2014-2017. | 1.3 | 20 |
| 16 | Realization of Third-Order OAM Mode Using Ring Patch Antenna. IEEE Transactions on Antennas and Propagation, 2020, 68, 7607-7611. | 3.1 | 20 |
| 17 | AlGaN-Based Deep Ultraviolet Vertical-Cavity Surface-Emitting Laser. IEEE Electron Device Letters, 2021, 42, 375-378. | 2.2 | 19 |
| 18 | Electrically injected GaN-based microdisk towards an efficient whispering gallery mode laser. Optics Express, 2021, 29, 5598. | 1.7 | 13 |

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| 19 | Optical gain based on NaYF4: Er3+, Yb3+ nanoparticles-doped polymer waveguide under convenient LED pumping. Applied Physics Letters, 2021, 118, . | 1.5 | 12 |
| 20 | Dynamics of carrier tunneling and recombination in asymmetric coupled InGaN multiple quantum wells. Optics Express, 2017, 25, 24745. | 1.7 | 11 |
| 21 | Photoluminescence of InGaN-based red multiple quantum wells. Optics Express, 2021, 29, 30237. | 1.7 | 11 |
| 22 | Low threshold lasing of GaN-based vertical cavity surface emitting lasers with an asymmetric coupled quantum well active region. Applied Physics Letters, 2008, 93, 191118. | 1.5 | 10 |
| 23 | Direct generation of 2-ps blue pulses from gain-switched InGaN VCSEL assessed by up-conversion technique. Scientific Reports, 2015, 4, 6401. | 1.6 | 10 |
| 24 | Tunable InGaN quantum dot microcavity light emitters with 129 nm tuning range from yellow-green to violet. Applied Physics Letters, 2017, 111, . | 1.5 | 8 |
| 25 | Green Vertical-Cavity Surface-Emitting Lasers Based on Combination of Blue-Emitting Quantum Wells and Cavity-Enhanced Recombination. IEEE Transactions on Electron Devices, 2018, 65, 4401-4406. | 1.6 | 8 |
| 26 | Leaky Wave Antenna Based on Periodically Truncated SSPP Waveguide. Plasmonics, 2020, 15, 551-558. | 1.8 | 8 |
| 27 | Effects of Lateral Optical Confinement In GaN VCSELs With Double Dielectric DBRs. IEEE Photonics Journal, 2020, 12, 1-8. | 1.0 | 8 |
| 28 | Optical properties of organic neodymium complex doped optical waveguides based on the intramolecular energy transfer effect. Optical Materials Express, 2020, 10, 2624. | 1.6 | 7 |
| 29 | Low-threshold wavelength-tunable ultraviolet vertical-cavity surface-emitting lasers from 376 to 409 nm. Fundamental Research, 2021, 1, 684-690. | 1.6 | 7 |
| 30 | Local Avalanche Effect of 4H-SiC p-i-n Ultraviolet Photodiodes With Periodic Micro-Hole Arrays. IEEE Electron Device Letters, 2022, 43, 64-67. | 2.2 | 7 |
| 31 | Low Threshold GaN-Based Microdisk Lasers on Silicon With High Q Factor. Journal of Lightwave Technology, 2022, 40, 2952-2958. | 2.7 | 7 |
| 32 | Emission dynamics of GaN-based blue resonant-cavity light-emitting diodes. Journal of Luminescence, 2019, 216, 116717. | 1.5 | 6 |
| 33 | Optical properties of InGaN-based red multiple quantum wells. Applied Physics Letters, 2022, 120, . | 1.5 | 6 |
| 34 | Impact of thickness of GaN buffer layer on properties of AlN/GaN distributed Bragg reflectors grown by metalorganic chemical vapor deposition. Science China Technological Sciences, 2010, 53, 313-316. | 2.0 | 5 |
| 35 | A Silicon-based On-chip Antenna Operating at 77GHz., 2019,,. | | 5 |
| 36 | Multiwavelength GaNâ€Based Surfaceâ€Emitting Lasers and Their Design Principles. Annalen Der Physik, 2020, 532, 1900308. | 0.9 | 5 |

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|----|--|-------------|-----------|
| 37 | Improvement of Thermal Dissipation of GaN-Based Micro Cavity Light-Emitting Devices. IEEE Photonics Technology Letters, 2021, 33, 19-22. | 1.3 | 5 |
| 38 | Simultaneous Analysis of Multi-Variables Effect on the Performance of Multi-Domain MFIS Negative Capacitance Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2021, 9, 741-747. | 1.2 | 5 |
| 39 | Optical Gain at 637 nm Wavelength in Polymer Waveguide Amplifier Under Commercial LED Pumping for Planar Photonic Integration. Advanced Optical Materials, 2022, 10, . | 3. 6 | 5 |
| 40 | Effect of barrier thickness on photoelectric properties of InGaN/GaN asymmetric multiple-quantum-well structure light-emitting diode. AIP Advances, 2022, 12, . | 0.6 | 5 |
| 41 | Reduction of Lasing Threshold of GaN-Based Vertical-Cavity Surface-Emitting Lasers by Using Short Cavity Lengths. IEEE Transactions on Electron Devices, 2018, 65, 2504-2508. | 1.6 | 4 |
| 42 | Large Rabi splitting in InGaN quantum wells microcavity at room temperature. Materials Research Express, 2019, 6, 076204. | 0.8 | 4 |
| 43 | Photoassisted chemical smoothing of AlGaN surface after laser lift-off. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2020, 38, . | 0.6 | 4 |
| 44 | High Q factor Electrically Injected Green Micro Cavity. Journal of Lightwave Technology, 2021, 39, 2895-2901. | 2.7 | 3 |
| 45 | InGaN-Based Orange-Red Resonant Cavity Light-Emitting Diodes. Journal of Lightwave Technology, 2022, 40, 4337-4343. | 2.7 | 3 |
| 46 | In-plane crystalline anisotropy of bulk \hat{l}^2 -Ga ₂ O ₃ . Journal of Applied Crystallography, 2021, 54, 1153-1157. | 1.9 | 2 |
| 47 | Investigation of CsPbBr ₃ CVD dynamics at various temperatures. Physical Chemistry Chemical Physics, 2021, 23, 23214-23218. | 1.3 | 2 |
| 48 | Effect of an inserted Al ₂ O ₃ passivation layer for atomic layer deposited HfO ₂ on indium phosphide. Semiconductor Science and Technology, 2021, 36, 125015. | 1.0 | 2 |
| 49 | Crystalline anisotropy of \hat{l}^2 -Ga ₂ O ₃ thin films on a c-plane GaN template and a sapphire substrate. Semiconductor Science and Technology, 2022, 37, 035003. | 1.0 | 2 |
| 50 | Thermal conductivity and phonon scattering of AlGaN nanofilms by elastic theory and Boltzmann transport equation. Semiconductor Science and Technology, 2022, 37, 055003. | 1.0 | 2 |
| 51 | Enhanced Light Emission due to Formation of Semi-polar InGaN/GaN Multi-quantum Wells. Nanoscale Research Letters, 2015, 10, 459. | 3.1 | 1 |
| 52 | Enhanced performances of vertical-structured green-band InGaN/GaN multiple-quantum-well solar cells with aluminum reflectors. Journal of the Korean Physical Society, 2016, 68, 1291-1294. | 0.3 | 1 |
| 53 | Impact of carbon nanotube pattern layers on gallium nitride-based light emitting diodes. Semiconductor Science and Technology, 2020, 35, 115013. | 1.0 | 1 |
| 54 | Room temperature continuous wave lasing of GaN-based green vertical-cavity surface-emitting lasers. , 2019, , . | | 1 |

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| 55 | Dual-wavelength switching in InGaN quantum dot micro-cavity light-emitting diodes. Optics Express, 2022, 30, 27472. | 1.7 | 1 |
| 56 | High-efficiency vertical-type InGaN/GaN multiple quantum well solar cells using aluminum reflectors. , $2016, , .$ | | 0 |
| 57 | Resonant cavity enhanced InGaN/GaN multiple quantum well solar cells. , 2016, , . | | 0 |
| 58 | Spoof surface plasmon polaritons characteristics of bandâ€stop slot resonators. Microwave and Optical Technology Letters, 0, , . | 0.9 | 0 |
| 59 | Mode tracking method based on information entropy prejudging mode swapping. AIP Advances, 2022, 12, 035334. | 0.6 | 0 |
| 60 | Realization of high-order modes on compact spoof surface plasmonic waveguide. , 2021, , . | | 0 |